

Amendments to the Claims:

Please amend claims 1, 13, 16 and 24 as follows. Following is a complete listing of the claims pending in the application, as amended:

1. (Currently Amended) A method of manufacturing a microelectronic device having a die with an integrated circuit, the method comprising:

forming a bond-pad on the die, wherein the bond-pad is electrically coupled to the integrated circuit;

forming a redistribution layer on the die, the redistribution layer including a conductive line having a first end portion attached to the bond-pad and a second end portion spaced apart from the bond-pad;

forming a passage through the die, the bond-pad, and the first end portion of the conductive line; and

depositing an electrically conductive material into at least a portion of the passage, wherein the electrically conductive material extends through the bond pad and contacts the bond-pad.

2. (Original) The method of claim 1, further comprising applying a passivation layer to at least a portion of the passage before depositing an electrically conductive material into at least a portion of the passage.

3. (Original) The method of claim 1, further comprising:

cleaning the passage after forming the passage through the die, the bond-pad, and the first end portion of the redistribution layer; and

applying a passivation layer to at least a portion of the passage before depositing an electrically conductive material into at least a portion of the passage.

4. (Original) The method of claim 1, further comprising applying a TiCl_4 TiN layer to at least a portion of the passage before depositing an electrically conductive material into at least a portion of the passage.

5. (Original) The method of claim 1, further comprising applying a wetting agent to at least a portion of the passage before depositing an electrically conductive material into at least a portion of the passage.

6. (Original) The method of claim 1, further comprising applying a Ni layer to at least a portion of the passage before depositing an electrically conductive material into at least a portion of the passage.

7. (Original) The method of claim 1, further comprising:
applying a TiCl_4 TiN layer to at least a portion of the passage; and
applying a Ni layer over at least a portion of the TiCl_4 TiN layer before depositing an electrically conductive material into at least a portion of the passage.

8. (Original) The method of claim 1, further comprising:
applying a passivation layer to at least a portion of the passage;
applying a TiCl_4 TiN layer over at least a portion of the passivation layer; and
applying a Ni layer over at least a portion of the TiCl_4 TiN layer before depositing an electrically conductive material into at least a portion of the passage.

9. (Original) The method of claim 1 wherein forming the passage includes laser-cutting a through-hole completely through the die.

10. (Original) The method of claim 1 wherein the bond-pad includes a hole filled with a passivation material, and wherein forming the passage includes laser-cutting a through-hole completely through the die and the passivation material.

11. (Original) The method of claim 1, further comprising:
forming a hole through the first end portion of the conductive line and the bond-pad; and
filling the hole with a passivation material, wherein forming the passage through the die, the bond-pad, and the first end portion of the conductive line

includes cutting a through-hole completely through the die and the passivation material.

12. (Original) The method of claim 1, further comprising:
etching a hole through the first end portion of the conductive line and the bond-pad; and
filling the hole with a passivation material, wherein forming the passage through the die, the bond-pad, and the first end portion of the conductive line includes laser-cutting a through-hole completely through the die and the passivation material.

13. (Currently Amended) ~~The method of claim 1, further comprising:~~A method of manufacturing a microelectronic device having a die with an integrated circuit, the method comprising:

forming a bond-pad on the die, wherein the bond-pad is electrically coupled to the integrated circuit;

forming a redistribution layer on the die, the redistribution layer including a conductive line having a first end portion attached to the bond-pad and a second end portion spaced apart from the bond-pad;

forming a passage through the die, the bond-pad, and the first end portion of the conductive line;

depositing an electrically conductive material into at least a portion of the passage, wherein the electrically conductive material extends through the bond pad;

forming a ball-pad on the second end portion of the conductive line; and
depositing a solder ball on the ball-pad.

14. (Original) The method of claim 1, further comprising forming a hole in the bond-pad before forming the passage through the die, the bond-pad, and the first end portion of the conductive line.

15. (Original) The method of claim 1, further comprising:
forming a hole in the bond-pad before forming the passage through the die, the bond-pad, and the first end portion of the conductive line; and
at least generally filling the first hole with a dielectric material, wherein forming the passage through the die, the bond-pad, and the first end portion of the conductive line includes forming the passage through the dielectric material.

16. (Currently Amended) A method of manufacturing a microelectronic device having a die with an integrated circuit and a bond-pad electrically coupled to the integrated circuit, the method comprising:
forming a passage completely through the die and the bond-pad; and
depositing an electrically conductive material into at least a portion of the passage, wherein the electrically conductive material contacts at least a portion of the bond-pad.

17. (Original) The method of claim 16 wherein the die includes a first surface and a second surface opposite to the first surface, wherein forming a bond-pad on the die includes forming a bond-pad at least proximate to the second surface, and wherein forming a passage through the die and the bond-pad includes applying a laser from the first surface of the die toward the second surface of the die to laser-cut a through-hole through the die.

18. (Original) The method of claim 16, further comprising applying a passivation layer to at least a portion of the passage before depositing an electrically conductive material into at least a portion of the passage.

19. (Original) The method of claim 16, further comprising applying a TiCl_4 TiN layer to at least a portion of the passage before depositing an electrically conductive material into at least a portion of the passage.

20. (Original) The method of claim 16, further comprising:
applying a TiCl_4 TiN layer to at least a portion of the passage; and
applying a Ni layer over at least a portion of the TiCl_4 TiN layer before depositing
an electrically conductive material into at least a portion of the passage.
21. (Original) The method of claim 16 wherein forming the passage includes
laser-cutting a through-hole at least through the die.
22. (Original) The method of claim 16, further comprising:
etching a hole through the bond-pad; and
filling the hole with a passivation material, wherein forming the passage through
the die and the bond-pad includes laser-cutting a through-hole through the
die and the passivation material.
23. (Original) The method of claim 16, further comprising forming a hole in
the bond-pad before forming the passage through the die and the bond-pad.
24. (Currently Amended) A method of forming a conductive interconnect in a
microfeature workpiece having a die, the die having an integrated circuit and a bond-
pad coupled to the integrated circuit, the method comprising:
forming a hole in the bond-pad;
forming a via completely through the die in alignment with the hole in the bond-
pad, wherein the via and the hole define a passage extending completely
through the die and the bond-pad; and
depositing an electrically conductive material into at least a portion of the
passage, wherein the electrically conductive material contacts at least a
portion of the bond-pad.
25. (Original) The method of claim 24, further comprising insulating the die
from the electrically conductive material in the passage.

26. (Original) The method of claim 24, further comprising applying an insulating layer to the die proximate to the passage to insulate the die from the electrically conductive material in the passage.

27. (Original) The method of claim 24, further comprising filling the hole in the bond-pad with a material, wherein forming a passage through the die and the bond-pad includes forming a passage through the die and the material filling the hole in the bond-pad.

28. (Original) The method of claim 24, further comprising filling the hole in the bond-pad with a passivation material, wherein forming a passage through the die and the bond-pad includes forming a passage through the die and the passivation material filling the hole in the bond-pad.

29. (Original) The method of claim 24 wherein forming a hole in the bond-pad includes forming a first hole having a first diameter, and wherein forming the passage includes laser-cutting a through-hole having a second diameter, the second diameter being less than the first diameter.

30. (Original) The method of claim 24, further comprising forming a conductive line electrically coupled to the bond-pad, wherein forming a passage through the die and the bond-pad includes forming a passage through a portion of the conductive line.

31-43. (Canceled)